

ZXMP6A17DN8

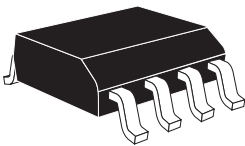
DUAL P-CHANNEL 60V ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -60V$; $R_{DS(ON)} = 0.125\Omega$; $I_D = -3.1A$

DESCRIPTION

This new generation of high cell density planar MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



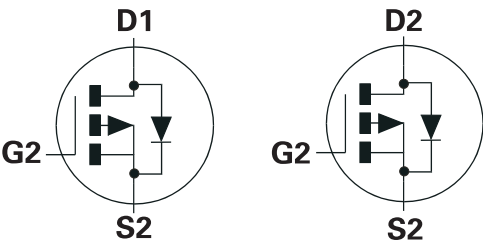
SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC-DC Converters
- Power Management functions
- Disconnect switches
- Motor control



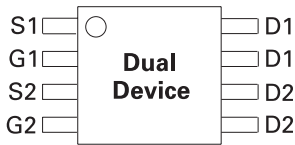
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXMP6A17DN8TA	7"	12mm	500 units
ZXMP6A17DN8TC	13"	12mm	2500 units

DEVICE MARKING

ZXMP
6A17D

PINOUT



Top view

ZXMP6A17DN8

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ (b)(d) @ $V_{GS}=10V$; $T_A=70^\circ C$ (b)(d) @ $V_{GS}=10V$; $T_A=25^\circ C$ (a)(d)	I_D	-3.1 -2.4 -2.3	A A A
Pulsed Drain Current (c)	I_{DM}	-11.1	A
Continuous Source Current (Body Diode)(b)	I_S	-3.0	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-11.1	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	P_D	1.25 10	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	P_D	1.81 14.5	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	P_D	2.15 17	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

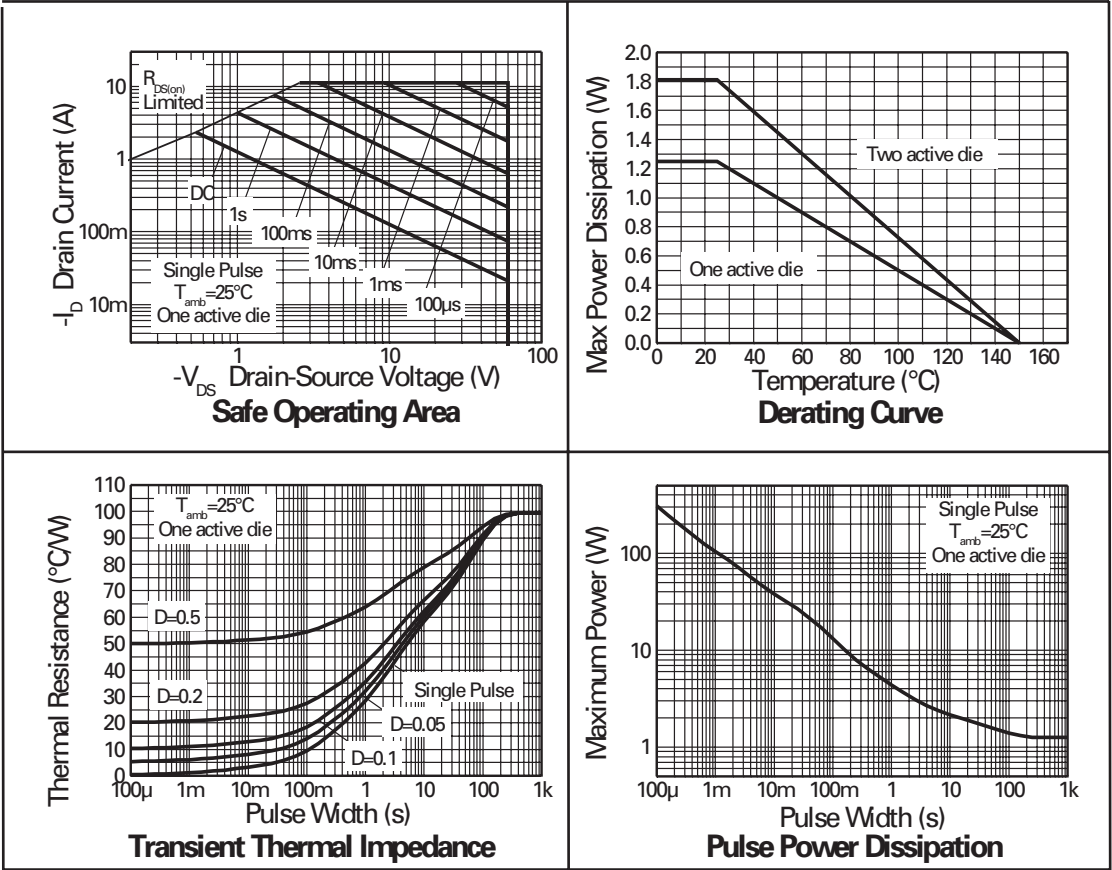
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (b)(e)	$R_{\theta JA}$	70	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	60	$^\circ C/W$

Notes

- (a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.
 (b) For a dual device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
 (c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width= $10\mu s$ - pulse width limited by maximum junction temperature.
 (d) For a dual device with one active die.
 (e) For dual device with 2 active die running at equal power.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

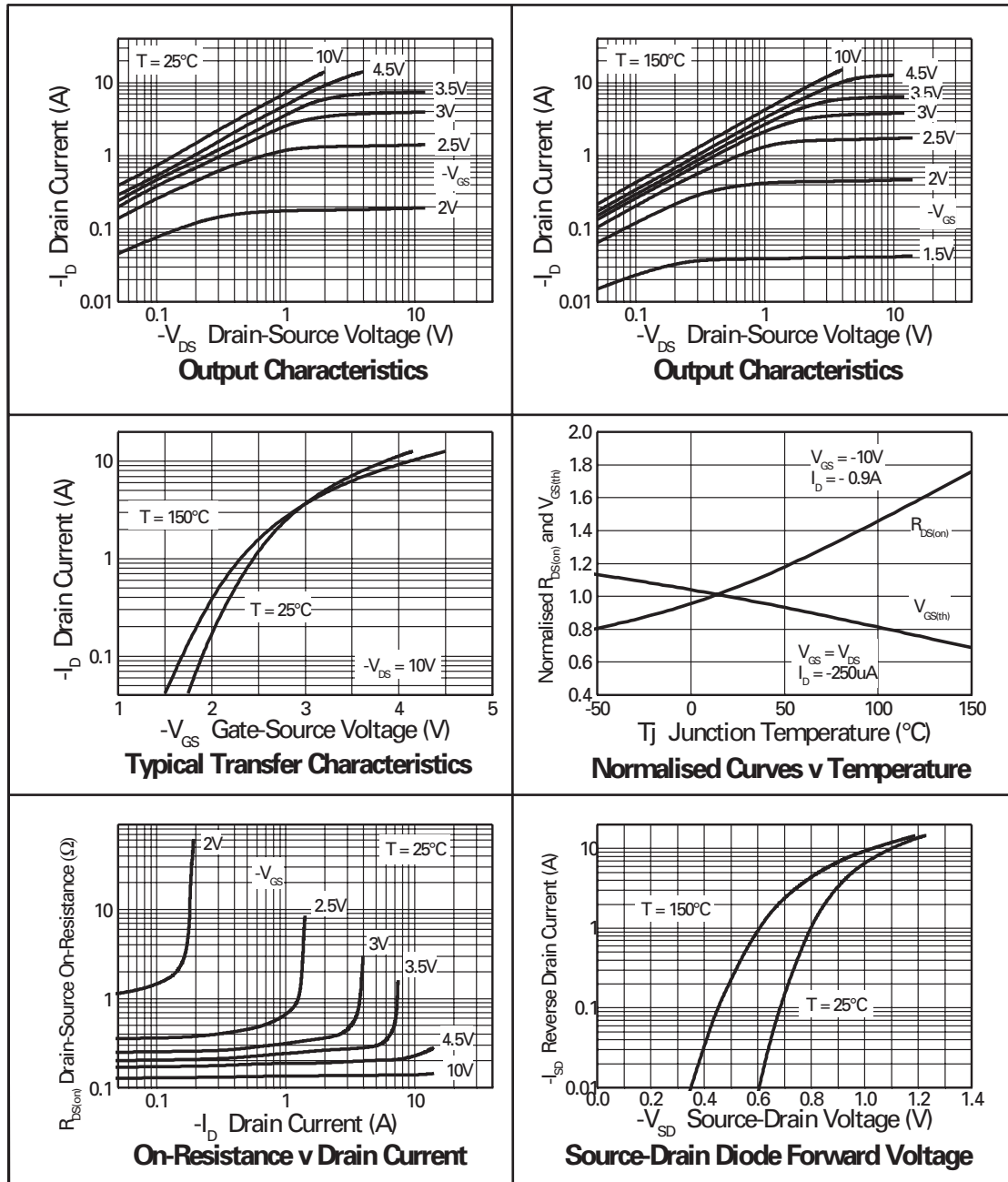
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-60			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	V _{DS} =-60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-0.8			V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.125 0.190	Ω Ω	V _{GS} =-10V, I _D =-2.2A V _{GS} =-4.5V, I _D =-1.8A
Forward Transconductance (1)(3)	g _{fs}		4.9		S	V _{DS} =-15V,I _D =-2.2A
DYNAMIC (3)						
Input Capacitance	C _{iss}		670		pF	V _{DS} =-30 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		46.7		pF	
Reverse Transfer Capacitance	C _{rss}		28.0		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.9		ns	V _{DD} = -30V, I _D =-1A R _G ≅ 6.0Ω, V _{GS} =-10V
Rise Time	t _r		22.4		ns	
Turn-Off Delay Time	t _{d(off)}		20.0		ns	
Fall Time	t _f		16.0		ns	
Gate Charge	Q _g		7.3		nC	V _{DS} =-30V,V _{GS} =-5V, I _D =-2.2A
Total Gate Charge	Q _g		15.1		nC	V _{DS} =-30V,V _{GS} =-10V, I _D =-2.2A
Gate-Source Charge	Q _{gs}		1.8		nC	
Gate-Drain Charge	Q _{gd}		1.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}		-0.85	-0.95	V	T _J =25°C, I _S =-2A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		26.4		ns	T _J =25°C, I _F =-1.7A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		32.7		nC	

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

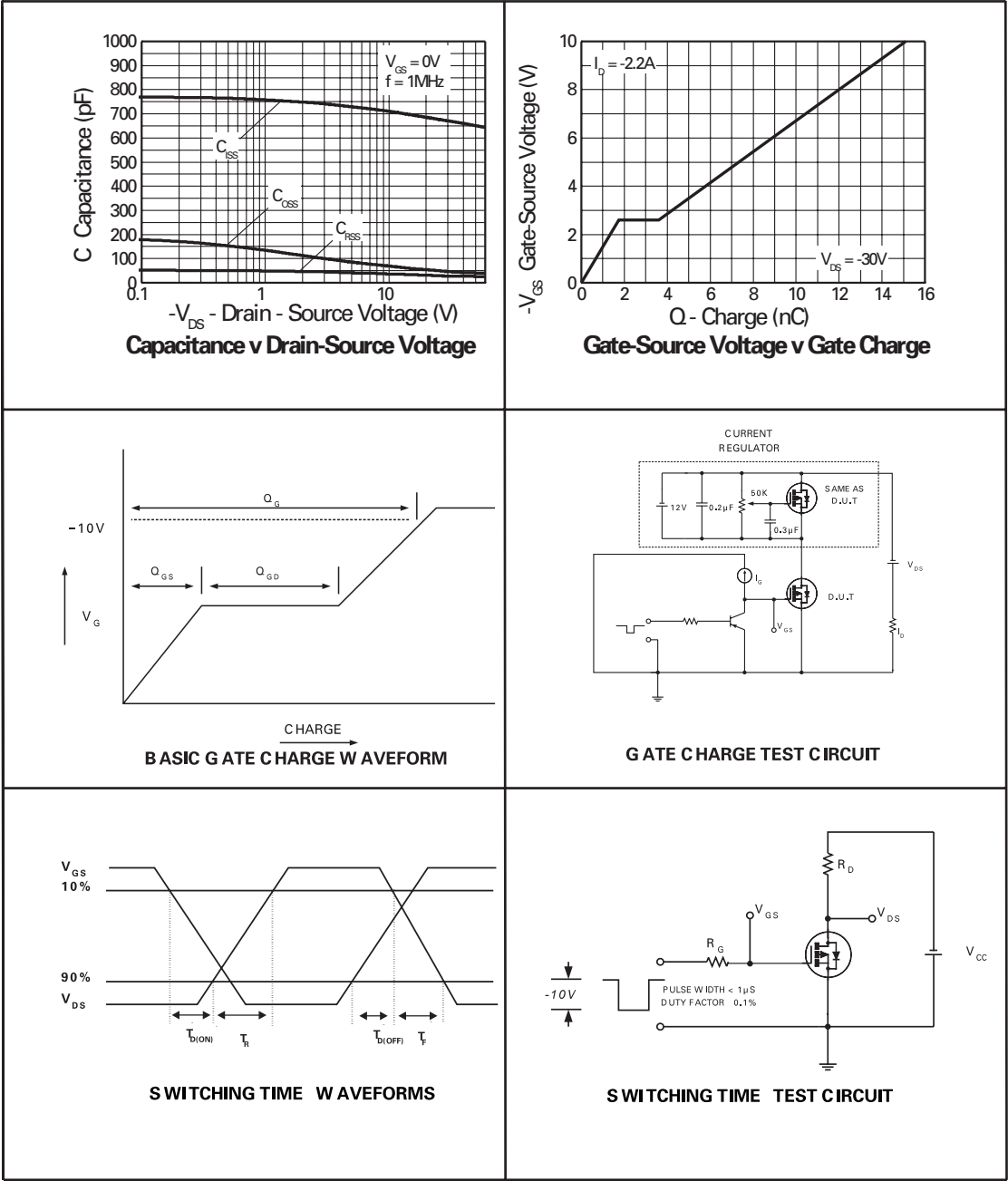
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TYPICAL CHARACTERISTICS



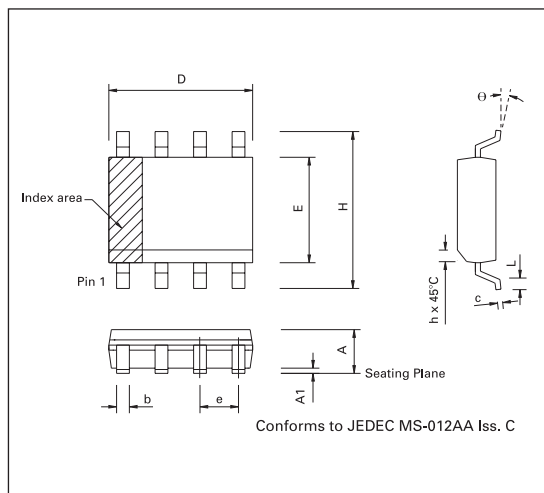
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TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETRES

PACKAGE DIMENSIONS

DIM	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A1	0.004	0.010	0.10	0.25
D	0.189	0.197	4.80	5.00
H	0.228	0.244	5.80	6.20
E	0.150	0.157	3.80	4.00
L	0.016	0.050	0.40	1.27
e	0.050 BSC		1.27 BSC	
b	0.013	0.020	0.33	0.51
c	0.008	0.010	0.19	0.25
Θ	0°	8°	0°	8°
h	0.010	0.020	0.25	0.50

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Europe

Zetex plc
Fields New Road
Chadderton
Oldham, OL9 8NP
United Kingdom
Telephone (44) 161 622 4422
Fax: (44) 161 622 4420
uk.sales@zetex.com

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany
Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49
europe.sales@zetex.com

Americas

Zetex Inc
700 Veterans Memorial Hwy
Hauppauge, NY11788
USA
Telephone: (631) 360 2222
Fax: (631) 360 8222
usa.sales@zetex.com

Asia Pacific

Zetex (Asia) Ltd
3701-04 Metroplaza, Tower 1
Hing Fong Road
Kwai Fong
Hong Kong
Telephone: (852) 26100 611
Fax: (852) 24250 494
asia.sales@zetex.com

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